



Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	097753,256
				Filing Date	December 28, 2000
				First Named Inventor	Valery M. Dubin
				Art Unit	2813
				Examiner Name	Nguyen, Tuan H.
				Attorney Docket Number	42390P10254
Sheet	2	of	3		

OTHER ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
TN		Brusic, "Copper Corrosion With and Without Inhibitors," J. Electrochem. Soc., Vol. 138, No. 8, pp. 2253-2258 (August 1991).	
TN		Cho, et al., "Copper Interconnection with Tungsten Cladding for ULSI," 1991 Symposium on VLSI Technology, pp. 39-40 (May 1991).	
TN		Cho, et al., "Electroless Cu for VLSI," MRS Bulletin, pp. 31-38 (June 1993).	
TN		Dubin, et al., "Selective Electroless Ni Deposition on a TiW Underlayer for Integrated Circuit Fabrication," Thin Solid Films, pp. 87-93 (1993).	
TN		Dubin, et al., "Selective and Blanket Electroless Cu Plating Initiated by Contact Displacement for Deep Submicron Via Contact Filling," VMIC Conference, pp. 315-321 (June 1995).	
TN		Gardner, et al., "Encapsulated Copper Interconnection Devices Using Sidewall Barriers," VMIC Conference, pp. 99-108 (June 1991).	
TN		Georgiou, et al., "Thick Selective Electroless-Plated Cobalt-Nickel Alloy Contacts to CoSi ₂ ," J. Electrochem. Soc., Vol. 138, No. 7, pp. 2061-2069 (July 1991).	
TN		Jagannathan, et al., "Electroless Plating of Copper at a Low pH Level," J. Res. Develop., Vol. 37, No. 2, pp. 117-123 (March 1993).	
TN		Kiang, et al., "Pd/Si Plasma Immersion Ion Implantation for Selective Electroless Copper Plating on SiO ₂ ," Appl. Phys. Lett., Vol. 60, No. 22, pp. 2767-2769.	
TN		Luther, et al., "Planar Copper-Polyimide Back End of the Line Interconnections for ULSI Devices," VMIC Conference, pp. 15-21 (June 1993).	
TN		Mak, "Electroless Copper Deposition on Metals and Metal Silicides," MRS Bulletin, pp. 55-62 (August 1994).	
TN		Murarka, et al., "Inlaid Copper Multilevel Interconnections Using Planarization by Chemical-Mechanical Polishing," MRS Bulletin, pp. 46-51 (June 1993).	
TN		Paunovic, et al., "Electrochemically Deposited Diffusion Barriers," J. Electrochem. Soc., Vol. 141, No. 7, pp. 1843-1850 (July 1994).	
TN		Shacham-Diamand, "100 nm Wide Copper Lines Made by Selective Electroless Deposition," J. Micromech. Microeng., pp. 66-72 (1991).	

Examiner Signature	T. NGUYEN	Date Considered	5/30/03
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Sheet	1	of	3
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Attorney Docket Number	42390P10254

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
TN		US-4,574,094	03-04-1986	DeLuca et al.	/
TN		US-4,574,095	03-04-1986	Baum et al.	//
TN		US-4,789,648	12-06-1988	Chow et al.	///
TN		US-4,894,260	01-16-1990	Kumasaka et al.	////
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TN		US-5,151,168	09-29-1992	Gilton et al.	//////
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FOREIGN PATENT DOCUMENTS

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